



MBR10H150CT, MBRF10H150CT & SB10H150CT-1

Vishay General Semiconductor

Dual Common-Cathode High-Voltage Schottky Rectifier

Low Leakage Current 5.0 μA



FEATURES

- Guardring for overvoltage protection
- Low power loss, high efficiency
- Low forward voltage drop
- High frequency operation
- Solder dip 260 °C, 40 seconds
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

TYPICAL APPLICATIONS

For use in high frequency inverters, free-wheeling and polarity protection applications.

MECHANICAL DATA

Case: TO-220AB, ITO-220AB, TO-262AA

Epoxy meets UL 94V-0 flammability rating

Terminals: Matte tin plated leads, solderable per J-STD-002B and JESD22-B102D

E3 suffix for commercial grade

Mounting Torque: 10 in-lbs maximum

Polarity: As marked

PRIMARY CHARACTERISTICS

$I_{F(AV)}$	2 x 5 A
V_{RRM}	150 V
I_{FSM}	160 A
V_F	0.72 V
T_j	175 °C

MAXIMUM RATINGS ($T_C = 25\text{ °C}$ unless otherwise noted)

PARAMETER	SYMBOL	MBR10H150CT	UNIT
Maximum repetitive peak reverse voltage	V_{RRM}	150	V
Working peak reverse voltage	V_{RWM}	150	V
Maximum DC blocking voltage	V_{DC}	150	V
Maximum average forward rectified current (see Fig. 1) Total device per diode	$I_{F(AV)}$	10 5	A
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode	I_{FSM}	160	A
Peak repetitive reverse current per diode at $t_p = 2\text{ }\mu\text{s}$, 1 kHz	I_{RRM}	1.0	A
Peak non-repetitive reverse surge energy per diode (8/20 μs waveform)	E_{RSM}	10	mJ
Non-repetitive avalanche energy per diode at 25 °C, $I_{AS} = 1.5\text{ A}$, $L = 10\text{ mH}$	E_{AS}	11.25	mJ
Voltage rate of change (rated V_R)	dv/dt	10000	V/ μs
Operating junction and storage temperature range	T_J, T_{STG}	- 65 to + 175	°C
Isolation voltage (ITO-220AB only) from terminals to heatsink $t = 1\text{ minute}$	V_{AC}	1500	V

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ELECTRICAL CHARACTERISTICS ($T_C = 25\text{ }^{\circ}\text{C}$ unless otherwise noted)				
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Maximum instantaneous forward voltage per diode ⁽¹⁾	at $I_F = 5.0\text{ A}$, $T_J = 25\text{ }^{\circ}\text{C}$	V_F	0.88	V
	at $I_F = 5.0\text{ A}$, $T_J = 125\text{ }^{\circ}\text{C}$		0.72	
	at $I_F = 10\text{ A}$, $T_J = 25\text{ }^{\circ}\text{C}$		0.96	
	at $I_F = 10\text{ A}$, $T_J = 125\text{ }^{\circ}\text{C}$		0.80	
Maximum reverse current per diode at working peak reverse voltage ⁽¹⁾	$T_J = 25\text{ }^{\circ}\text{C}$	I_R	5.0	μA
	$T_J = 125\text{ }^{\circ}\text{C}$		1.0	mA

Note:

(1) Pulse test: 300 μs pulse width, 1 % duty cycle

THERMAL CHARACTERISTICS ($T_C = 25\text{ }^{\circ}\text{C}$ unless otherwise noted)					
PARAMETER	SYMBOL	MBR	MBRF	MBRB	UNIT
Typical thermal resistance per diode	$R_{\theta JC}$	2.4	4.5	2.4	$^{\circ}\text{C/W}$

ORDERING INFORMATION (Example)					
PACKAGE	PREFERRED P/N	UNIT WEIGHT (g)	PACKAGE CODE	BASE QUANTITY	DELIVERY MODE
TO-220AB	MBR10H150CT-E3/45	2.06	45	50/Tube	Tube
ITO-220AB	MBRF10H150CT-E3/45	2.20	45	50/Tube	Tube
TO-262AA	SB10H150CT-1E3/45	1.58	45	50/Tube	Tube

RATINGS AND CHARACTERISTICS CURVES

($T_A = 25\text{ }^{\circ}\text{C}$ unless otherwise noted)

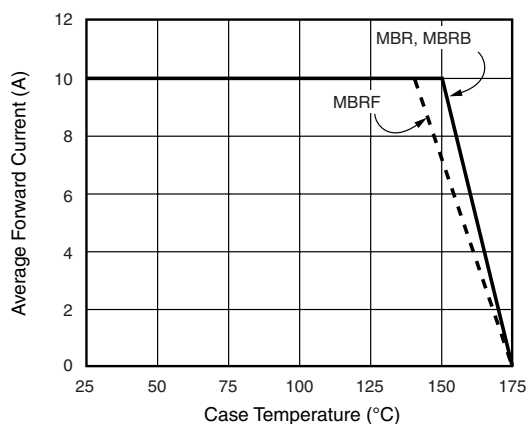


Figure 1. Forward Derating Curve (Total)

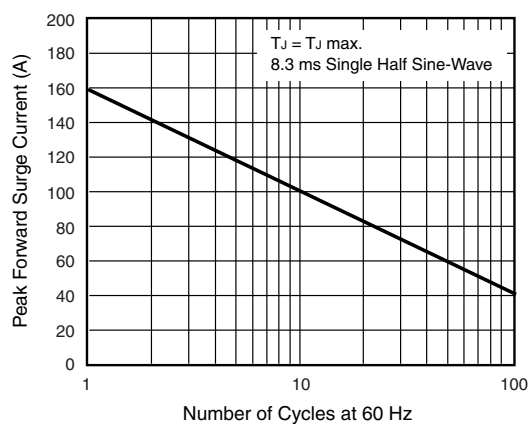


Figure 2. Maximum Non-Repetitive Peak Forward Surge Current Per Diode



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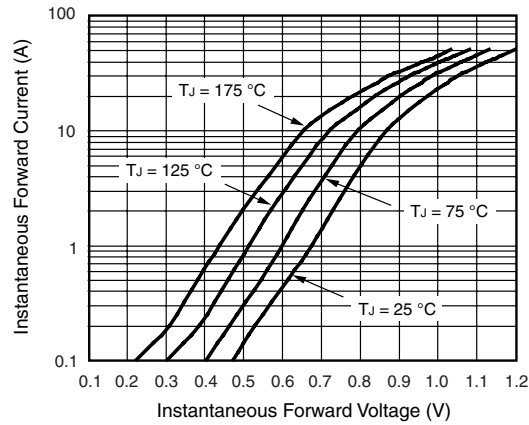


Figure 3. Typical Instantaneous Forward Characteristics Per Diode

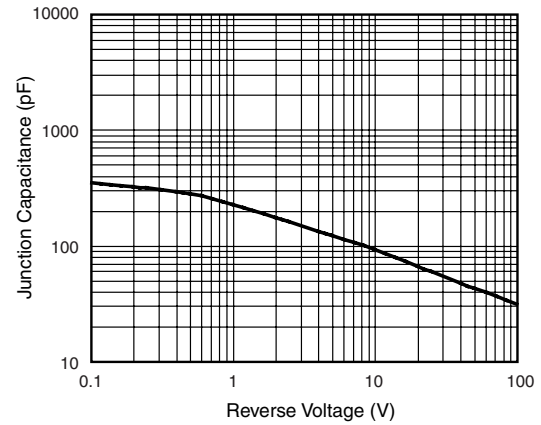


Figure 5. Typical Junction Capacitance Per Diode

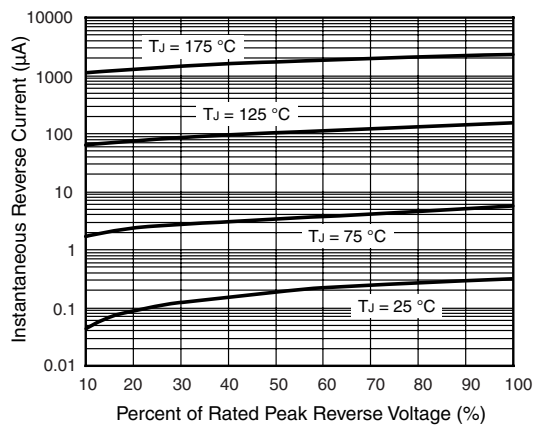


Figure 4. Typical Reverse Characteristics Per Diode

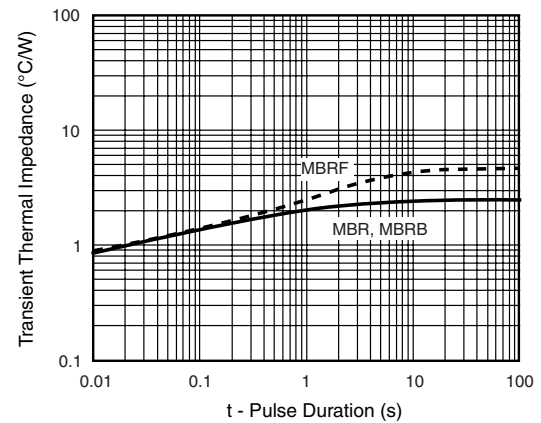


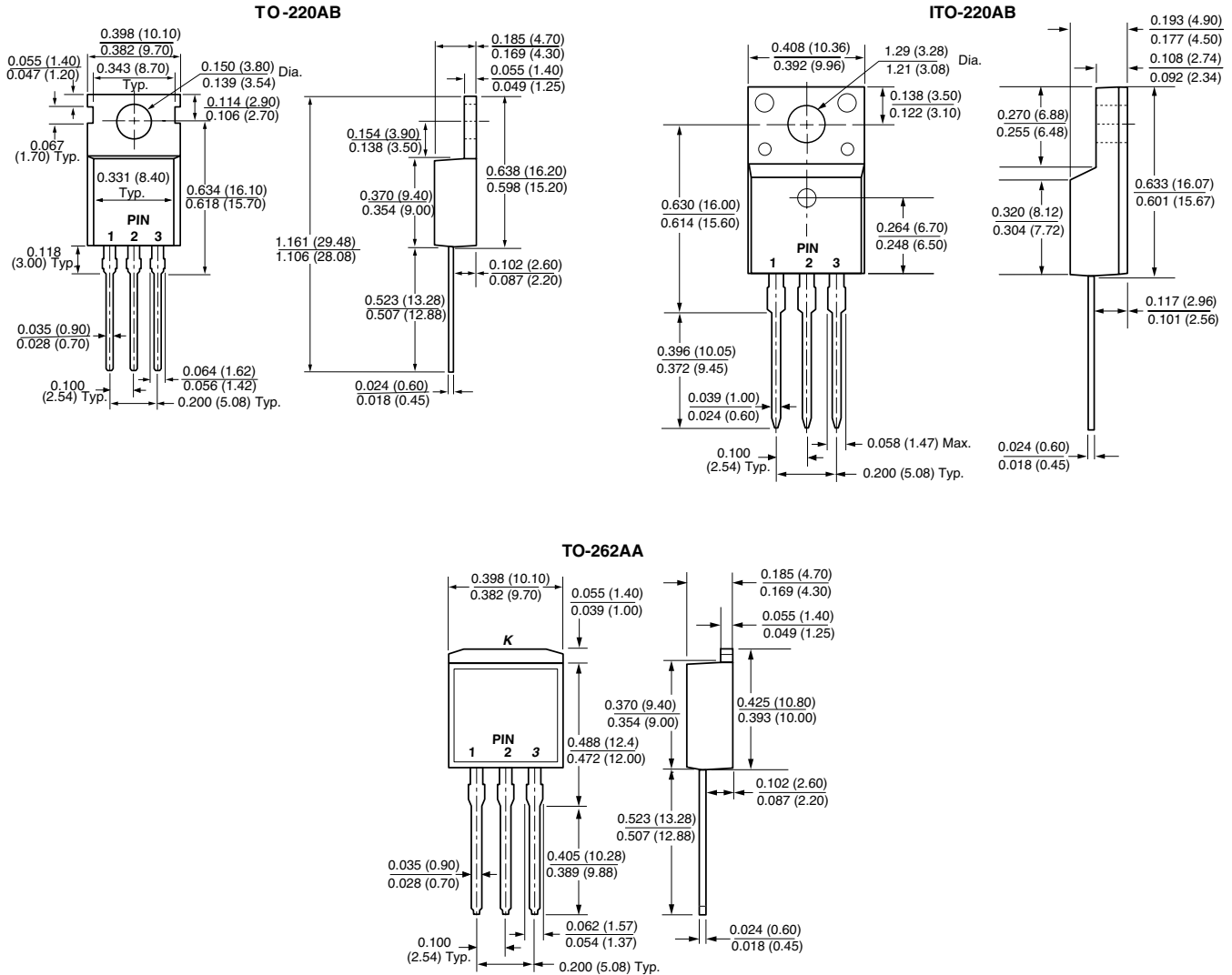
Figure 6. Typical Transient Thermal Impedance Per Diode

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PACKAGE OUTLINE DIMENSIONS in inches (millimeters)





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